



## NTE2665 **Silicon NPN Transistor Horizontal Deflection Output for High Resolution Display, Color TV**

#### Features:

High Voltage: V<sub>CBO</sub> = 1700V
Low Saturation Voltage: V<sub>CE(sat)</sub> = 3V Max
High Speed: t<sub>f</sub> = 0.1µs Typ

Absolute Maximum Ratings: (T <sub>C</sub> = +25°C unless otherwise specified)	
Collector-Base Voltage, V <sub>CBO</sub>	. 1700V
Collector-Emitter Voltage, V <sub>CEO</sub>	800V
Emitter-Base Voltage, V <sub>EBO</sub>	5V
Collector Current, I <sub>C</sub>	
Continuous	
Pulsed	
Base Current, I <sub>B</sub>	14A
Collector Power Dissipation, P <sub>C</sub>	. 220W
Operating Junction Temperature, T <sub>J</sub>	+150°C
Storage Temperature Range, T <sub>stg</sub> 55° to	+150°C

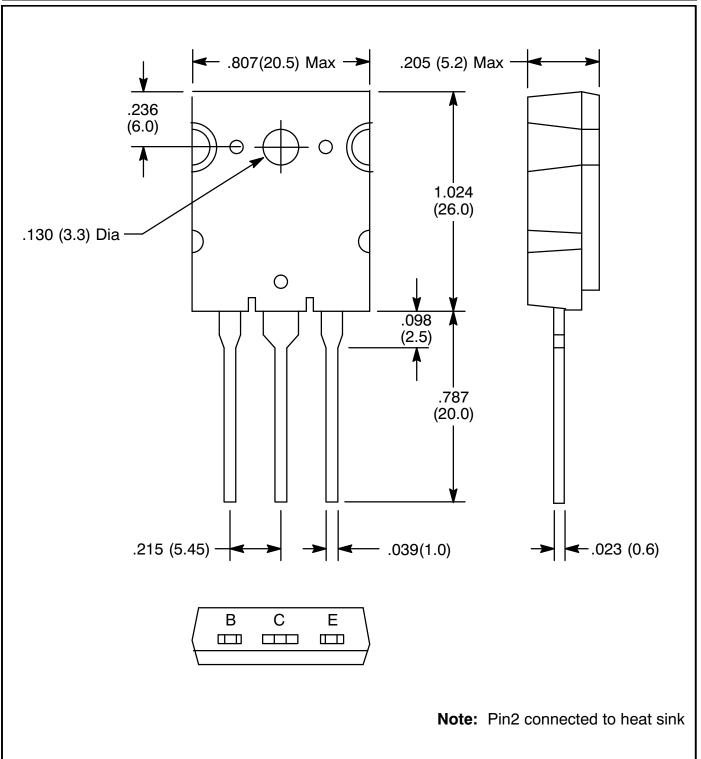
Note 1. Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the "Absolute Maximum Ratings".

### **<u>Electrical Chracteristics:</u>** (T<sub>C</sub> = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = 1700V, I <sub>E</sub> = 0	-	-	1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB} = 5V, I_{C} = 0$	-	-	100	μΑ
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_C = 10 \text{mA}, I_B = 0$	800	-	-	V
DC Current Gain	h <sub>FE</sub>	$V_{CE} = 5V$ , $I_C = 2A$	22	-	48	
		$V_{CE} = 5V$ , $I_C = 8A$	12.5	-	25.0	
		V <sub>CE</sub> = 5V, I <sub>C</sub> = 22A	4.5	-	7.5	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 22A, I_B = 5.5A$	-	-	3	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	$I_C = 22A, I_B = 5.5A$	-	1.0	1.5	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA	-	2	_	MHz
Collector Outptut Capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	-	470	-	pF

# **Electrical Chracteristics (Cont'd):** $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Switching Time						
Storage Time	t <sub>stg</sub>	$I_{CP} = 10A$ , $I_{B1}$ (end) = 1.4A, $f_H = 64$ kHz	-	2.6	3.0	μs
Fall Time	t <sub>f</sub>		-	0.2	0.3	μs
Storage Time	t <sub>stg</sub>	$I_{CP}$ = 8A, $I_{B1}$ (end) = 1.2A, $f_{H}$ = 130kHz	-	1.4	1.6	μs
Fall Time	t <sub>f</sub>		-	0.10	0.15	μs



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